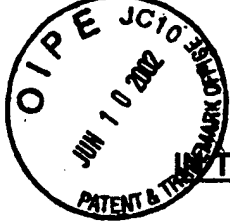


Serial No.: 09/902,429

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PATENT

Case No: F0588



THE UNITED STATES PATENT AND TRADEMARK OFFICE

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JUN 19 2002  
TECHNOLOGY CENTER 2800

In re application of: Qi Xiang

Serial No.: 09/902,429

Filing Date: July 10, 2001

For: SILICON ON INSULATOR FIELD EFFECT TRANSISTOR WITH  
HETEROJUNCTION GATE.

Examiner: Laura M. Schillinger

Art Unit: 2813

Box Non Fee Amendment  
Assistant Commissioner for Patents  
Washington, D.C. 20231

**RESPONSE TO OFFICE ACTION DATED MARCH 19, 2002**

Examiner:

The applicants respectfully request favorable reconsideration of the application  
in view of the following amendments and comments.

**AMENDMENTS**

**IN THE CLAIMS:**

Please add new claims 22-27 as follows:

22. (New) The transistor structure of claim 1, wherein the gate extends the entire  
length of the channel region between the source region and the drain region.